IN THE SPECIFICATION

Please replace the paragraph at page 3 line 23 through page 4 line 10 with the following paragraph.

One or more etching components can be arranged to correspond to a particular wafer portion. Alternatively, one or more etching components can be employed to etch various wafer portions. The etching components may be, for example, a gas plasma apparatus employed in reactive ion etching. It is to be appreciated that any suitable etching components may be employed with the present invention. For example, components employed in performing a main etch, or during a trim etch (*e.g.*, etch step before main etch (*e.g.*, descum etch), PR (photoresist) trim, BARC (breakthrough anti-reflective coating)) may be employed in accordance with the present invention. The etching components are selectively driven by the system to etch away oxide and/or other materials at a desired location, at a desired rate, to a desired depth and/or to a desired width. The etching progress is monitored by the system by comparing the critical dimensions (*e.g.*, space between features and/or gratings, depth and/or height of the features and/or gratings) on the wafer to desired critical dimensions. Data gathered during such monitoring can be analyzed to determine whether adaptations to the etch process are desired. As a result, more optimal etching is achieved by controlling the etching components that are etching the portions of the wafer, which in turn increases IC quality. Additionally, and/or alternatively, data concerning etch process conditions that resulted in favorable and/or unfavorable CDs can be stored to facilitate reproducing favorable etch process conditions for subsequent portions of the wafer being etched and/or for subsequent wafers.